Electronic Supplementary Material (ESI) for Nanoscale.
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Electronic Supplementary Information

Fully Gravure Printed Complementary Carbon Nanotube TFTs for Clock Signal Generator Using Epoxy-Imine Based Cross-linker as *n*-Dopant and Encapsulant

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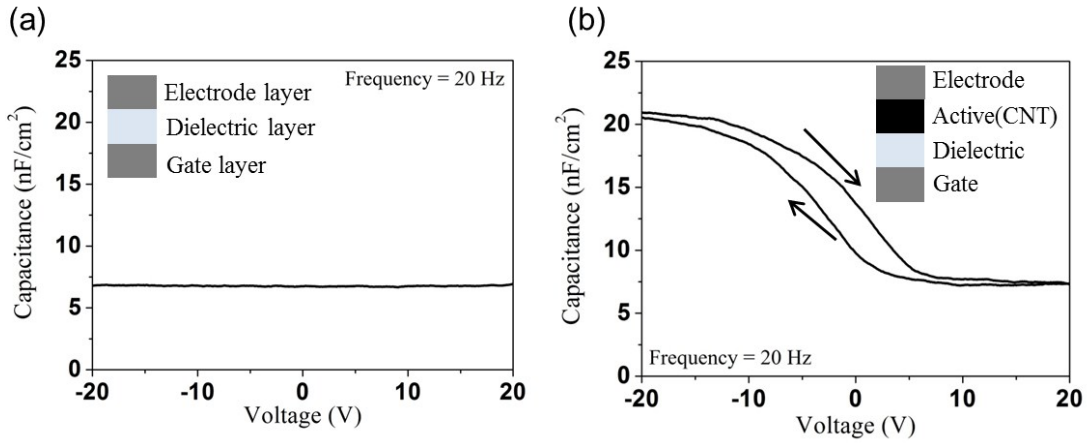

Figure S1. (a) C-V measurement curve of the printed dielectric layer (capacitance was 7 nF/cm^2 at ± 20V) and (b) the printed dielectric/SWNTs layers (capacitance was 20.5 nF/cm^2 at -20 V and dropped to 7.3 nF/cm^2 at 20 V).

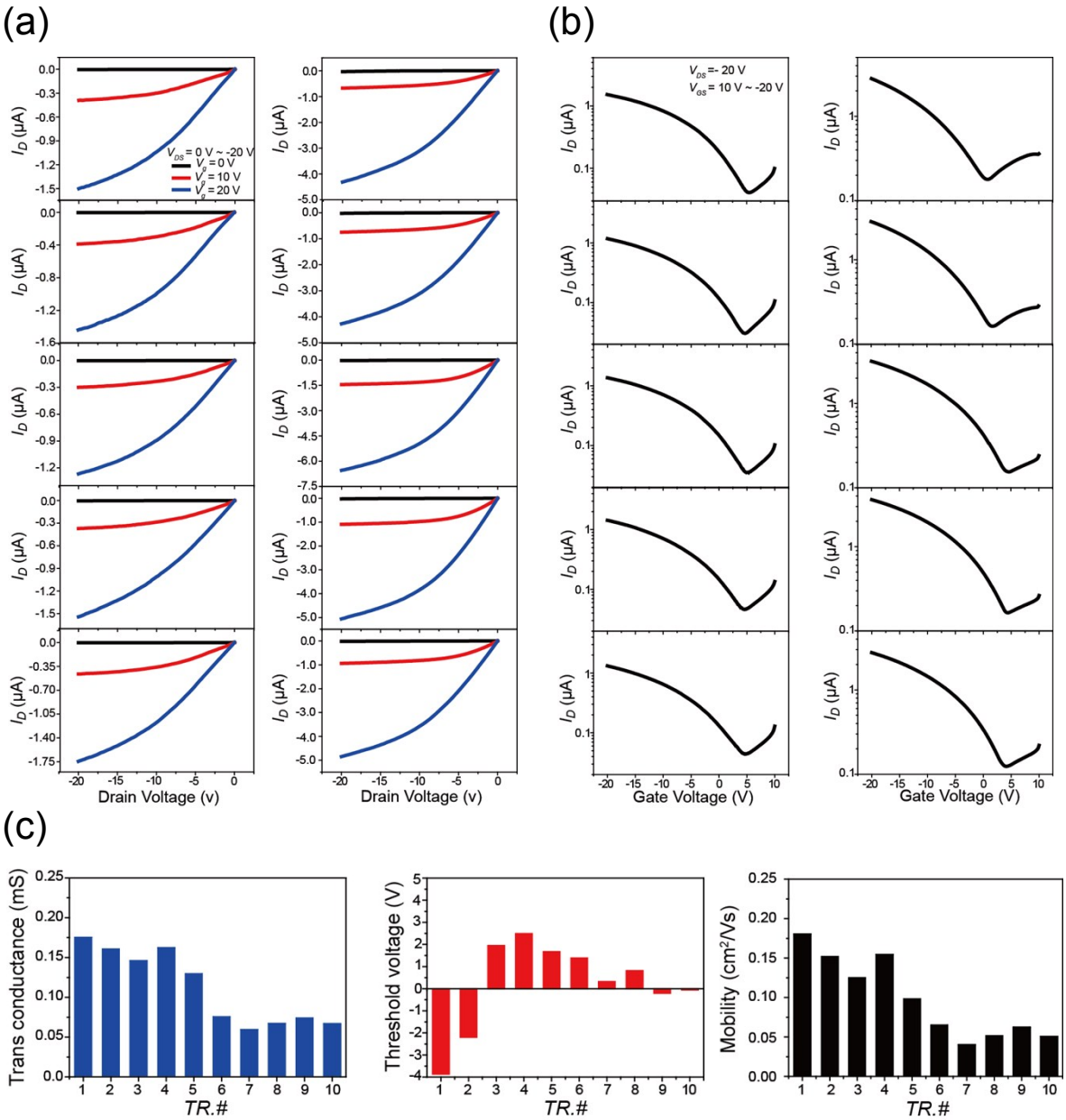

Figure S2. (a) Output and (b) transfer characteristics of the 10 fully gravure-printed *p*-type SWCNT-TFTs used in the CMOS ring oscillator prior to n-type doping with (c) their extracted transconductance, threshold voltage, and mobility.

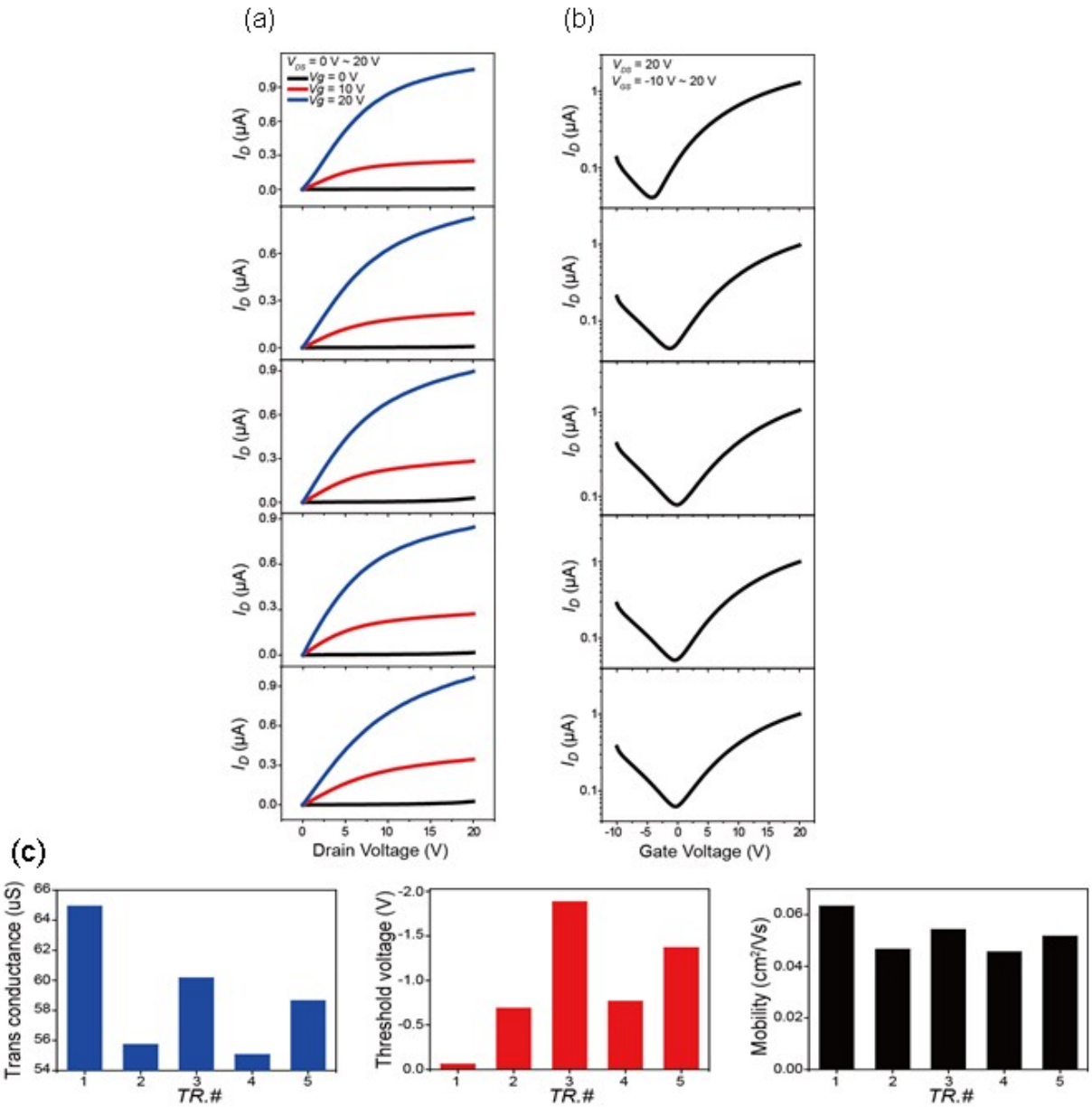

Figure S3. (a) Output and (b) transfer characteristics of 5 fully gravure-printed *n*-type SWCNT-TFTs with (c) their extracted transconductance, threshold voltage, and mobility.

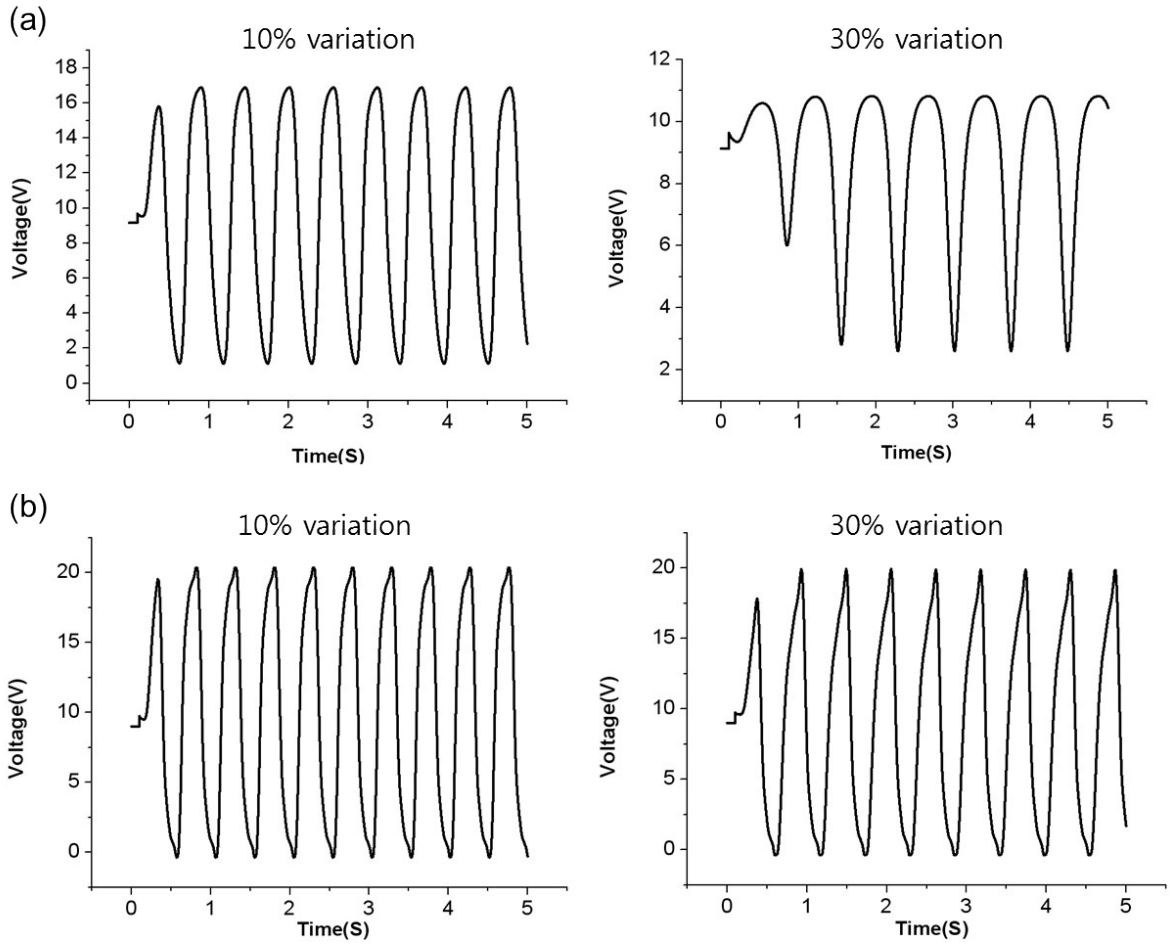

Figure S4. Simulation data of comparison of the PMOS (a) and CMOS (b) ring oscillators with variation of the center currents from I_{ds}-V_{ds} of *n* and *p*-type TFTs from 10% to 30%.